

# Daniela Munteanu

## List of Publications by Year in descending order

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citations

236925

25  
h-index

289244

40  
g-index

155  
all docs

155  
docs citations

155  
times ranked

1245  
citing authors

#	ARTICLE	IF	CITATIONS
1	Real-Time Characterization of Neutron-Induced SEUs in Fusion Experiments at WEST Tokamak During D-D Plasma Operation. IEEE Transactions on Nuclear Science, 2022, 69, 501-511.	2.0	4
2	Electronics reliability assessment of future power fusion machines: Neutron interaction analysis in bulk silicon. Microelectronics Reliability, 2021, 126, 114223.	1.7	2
3	Basic single-event mechanisms in Ge-based nanoelectronics subjected to terrestrial atmospheric neutrons. Microelectronics Reliability, 2021, , 114256.	1.7	0
4	Atmospheric Neutron Radiation Response of III-V Binary Compound Semiconductors. IEEE Transactions on Nuclear Science, 2020, 67, 1428-1435.	2.0	13
5	Modelling and simulation of SEU in bulk Si and Ge SRAM. Microelectronics Reliability, 2019, 100-101, 113390.	1.7	1
6	Terrestrial neutron-induced single events in GaN. Microelectronics Reliability, 2019, 100-101, 113357.	1.7	3
7	A water tank muon spectrometer for the characterization of low energy atmospheric muons. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 933, 12-17.	1.6	1
8	Characterization of atmospheric muons at sea level using a cosmic ray telescope. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2018, 903, 77-84.	1.6	12
9	Single-event-transient effects in Junctionless Double-Gate MOSFETs with Dual-Material Gate investigated by 3D simulation. Microelectronics Reliability, 2017, 76-77, 719-724.	1.7	8
10	Multi-Poisson process analysis of real-time soft-error rate measurements in bulk 65 nm and 40 nm SRAMs. Microelectronics Reliability, 2017, 76-77, 53-57.	1.7	3
11	Natural radiation events in CCD imagers at ground level. Microelectronics Reliability, 2016, 64, 68-72.	1.7	4
12	Real-time soft error rate measurements on bulk 40 nm SRAM memories: a five-year dual-site experiment. Semiconductor Science and Technology, 2016, 31, 114003.	2.0	3
13	Radiation and COTS at ground level. Microelectronics Reliability, 2015, 55, 2147-2153.	1.7	3
14	3D simulation of single-event-transient effects in symmetrical dual-material double-gate MOSFETs. Microelectronics Reliability, 2015, 55, 1522-1526.	1.7	7
15	SEU sensitivity of Junctionless Single-Gate SOI MOSFETs-based 6T SRAM cells investigated by 3D TCAD simulation. Microelectronics Reliability, 2015, 55, 1501-1505.	1.7	1
16	ASTEP (2005-2015): Ten years of soft error and atmospheric radiation characterization on the Plateau de Bure. Microelectronics Reliability, 2015, 55, 1506-1511.	1.7	7
17	Random-Walk Drift-Diffusion Charge-Collection Model For Reverse-Biased Junctions Embedded in Circuits. IEEE Transactions on Nuclear Science, 2014, 61, 3527-3534.	2.0	15
18	Altitude and Underground Real-Time SER Testing of SRAMs Manufactured in CMOS Bulk 130, 65 and 40 nm. , 2014, , .		6

#	ARTICLE	IF	CITATIONS
19	Use of CCD to Detect Terrestrial Cosmic Rays at Ground Level: Altitude vs. Underground Experiments, Modeling and Numerical Monte Carlo Simulation. IEEE Transactions on Nuclear Science, 2014, 61, 3380-3388.	2.0	8
20	Behavioral modeling of SRIM tables for numerical simulation. Nuclear Instruments & Methods in Physics Research B, 2014, 322, 2-6.	1.4	25
21	Real-time soft-error rate measurements: A review. Microelectronics Reliability, 2014, 54, 1455-1476.	1.7	27
22	Particle Monte Carlo modeling of single-event transient current and charge collection in integrated circuits. Microelectronics Reliability, 2014, 54, 2278-2283.	1.7	8
23	Radiation sensitivity of junctionless double-gate 6T SRAM cells investigated by 3-D numerical simulation. Microelectronics Reliability, 2014, 54, 2284-2288.	1.7	17
24	Application of the TIARA Radiation Transport Tool to Single Event Effects Simulation. IEEE Transactions on Nuclear Science, 2014, 61, 1498-1500.	2.0	87
25	Soft errors induced by natural radiation at ground level in floating gate flash memories. , 2013, , .		12
26	Technology downscaling worsening radiation effects in bulk: SOI to the rescue. , 2013, , .		85
27	Scaling of high- $\kappa$ /metal-gate TriGate SOI nanowire transistors down to 10nm width. Solid-State Electronics, 2013, 88, 32-36.	1.4	17
28	3-D Numerical Simulation of Bipolar Amplification in Junctionless Double-Gate MOSFETs Under Heavy-Ion Irradiation. IEEE Transactions on Nuclear Science, 2012, 59, 773-780.	2.0	35
29	Electronic transport in GAA silicon nanowire MOSFETs: From Kubo-Greenwood mobility including screening remote coulomb scattering to analytical backscattering coefficient. , 2012, , .		1
30	Geant4 Analysis of n-Si Nuclear Reactions From Different Sources of Neutrons and Its Implication on Soft-Error Rate. IEEE Transactions on Nuclear Science, 2012, 59, 714-722.	2.0	31
31	A review of real-time soft-error rate measurements in electronic circuits. , 2012, , .		8
32	Real-time Soft-Error testing of 40nm SRAMs. , 2012, , .		25
33	Simulation Analysis of Bipolar Amplification in Independent-Gate FinFET and Multi-Channel NWFET Submitted to Heavy-Ion Irradiation. IEEE Transactions on Nuclear Science, 2012, 59, 3249-3257.	2.0	5
34	Soft-Error Rate Induced by Thermal and Low Energy Neutrons in 40 nm SRAMs. IEEE Transactions on Nuclear Science, 2012, 59, 2658-2665.	2.0	40
35	Underground Experiment and Modeling of Alpha Emitters Induced Soft-Error Rate in CMOS 65 nm SRAM. IEEE Transactions on Nuclear Science, 2012, 59, 1048-1053.	2.0	21
36	Kubo-Greenwood approach for the calculation of mobility in gate-all-around nanowire metal-oxide-semiconductor field-effect transistors including screened remote Coulomb scatteringâ€”Comparison with experiment. Journal of Applied Physics, 2012, 111, 103710.	2.5	11

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37	The Plateau de Bure Neutron Monitor: Design, Operation and Monte Carlo Simulation. IEEE Transactions on Nuclear Science, 2012, 59, 303-313.	2.0	13
38	Alpha-Particle Induced Soft-Error Rate in CMOS 130 nm SRAM. IEEE Transactions on Nuclear Science, 2011, 58, 1086-1092.	2.0	12
39	Analytical model of ballistic current for GAA nanowire MOSFET including band structure effects: Application to ring oscillator. , 2011, , .		1
40	3-D numerical simulation of bipolar amplification in Junctionless Double-Gate MOSFETs under heavy-ion irradiation. , 2011, , .		3
41	Modeling of energy bands in ultra-thin layer quantum nanostructures for solar cell applications. Journal of Non-Crystalline Solids, 2011, 357, 1884-1887.	3.1	8
42	Effects of localized gate stack parasitic charge on current-voltage characteristics of double-gate MOSFETs with high-permittivity dielectrics and Ge-channel. Journal of Non-Crystalline Solids, 2011, 357, 1879-1883.	3.1	1
43	Numerical Simulation of Transient Response in 3-D Multi-Channel Nanowire MOSFETs Submitted to Heavy Ion Irradiation. , 2011, , .		1
44	Simulation study of Short-Channel Effects and quantum confinement in double-gate FinFET devices with high-mobility materials. Microelectronic Engineering, 2011, 88, 366-369.	2.4	12
45	Quantum Compact Model of Drain Current in Independent Double-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 024301.	1.5	0
46	Analytical Modeling of Alpha-Particle Emission Rate at Wafer-Level. IEEE Transactions on Nuclear Science, 2011, 58, 2798-2803.	2.0	10
47	Analytical model of drain current in nanowire MOSFETs including quantum confinement, band structure effects and quasi-ballistic transport: device to circuit performances analysis. , 2011, , .		8
48	Impact of (Quasi-)Ballistic Transport on Operation of Complementary Metalâ€“Oxideâ€“Semiconductor Inverters Based on Fully-Depleted Silicon-on-Insulator and Nanowire Devices. Japanese Journal of Applied Physics, 2011, 50, 014103.	1.5	0
49	Impact of (Quasi-)Ballistic Transport on Operation of Complementary Metalâ€“Oxideâ€“Semiconductor Inverters Based on Fully-Depleted Silicon-on-Insulator and Nanowire Devices. Japanese Journal of Applied Physics, 2011, 50, 014103.	1.5	0
50	Quantum Compact Model of Drain Current in Independent Double-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 024301.	1.5	1
51	Soft-errors induced by terrestrial neutrons and natural alpha-particle emitters in advanced memory circuits at ground level. Microelectronics Reliability, 2010, 50, 1822-1831.	1.7	34
52	Alpha-emitter induced soft-errors in CMOS 130nm SRAM: Real-time underground experiment and Monte-Carlo simulation. , 2010, , .		1
53	A GPU/CUDA implementation of the collection-diffusion model to compute SER of large area and complex circuits. , 2010, , .		7
54	A Simple Compact Model to Analyze the Impact of Ballistic and Quasi-Ballistic Transport on Ring Oscillator Performance. Lecture Notes in Electrical Engineering, 2010, , 37-51.	0.4	0

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55	Evidences on the Physical Origin of the Unexpected Transport Degradation in Ultimate n-FDSOI Devices. IEEE Nanotechnology Magazine, 2009, 8, 167-173.	2.0	11
56	Combined altitude and underground real-time SER characterization of CMOS technologies on the ASTEP-LSM platform. , 2009, , .		4
57	Altitude and Underground Real-Time SER Characterization of CMOS 65 nm SRAM. IEEE Transactions on Nuclear Science, 2009, 56, 2258-2266.	2.0	52
58	Simulation of Gate Tunneling Current in Metal-Insulator-Metal Capacitor with Multi layer High- $\epsilon_r$ Dielectric Stack Using the Non-equilibrium Green's Function Formalism. Japanese Journal of Applied Physics, 2009, 48, 111409.	1.5	3
59	Analytical modelling and performance analysis of double-gate MOSFET-based circuit including ballistic/quasi-ballistic effects. Molecular Simulation, 2009, 35, 631-637.	2.0	1
60	Quantum Simulation of C-V and I-V Characteristics in Ge and III-V Materials/High- $\epsilon_r$ MOS Devices. Materials Research Society Symposia Proceedings, 2009, 1194, 15.	0.1	0
61	Experimental Investigation on the Quasi-Ballistic Transport: Part I- Determination of a New Backscattering Coefficient Extraction Methodology. IEEE Transactions on Electron Devices, 2009, 56, 408-419.	3.0	43
62	Experimental Investigation on the Quasi-Ballistic Transport: Part II- Backscattering Coefficient Extraction and Link With the Mobility. IEEE Transactions on Electron Devices, 2009, 56, 420-430.	3.0	43
63	Physics-Based Analytical Modeling of Quasi-Ballistic Transport in Double-Gate MOSFETs: From Device to Circuit Operation. IEEE Transactions on Electron Devices, 2009, 56, 2692-2702.	3.0	16
64	Investigation of capacitance-voltage characteristics in Ge /high- $\epsilon_r$ MOS devices. Journal of Non-Crystalline Solids, 2009, 355, 1171-1175.	3.1	15
65	Simulation study of circuit performances of independent double-gate (IDG) MOSFETs with high-permittivity gate dielectrics. Journal of Non-Crystalline Solids, 2009, 355, 1185-1188.	3.1	3
66	Electron transport through high- $\epsilon_r$ dielectric barriers: A non-equilibrium Green's function (NEGF) study. Journal of Non-Crystalline Solids, 2009, 355, 1180-1184.	3.1	6
67	3-D Simulation Analysis of Bipolar Amplification in Planar Double-Gate and FinFET With Independent Gates. IEEE Transactions on Nuclear Science, 2009, 56, 2083-2090.	2.0	31
68	A compact model for the ballistic subthreshold current in ultra-thin independent double-gate MOSFETs. Molecular Simulation, 2009, 35, 491-497.	2.0	3
69	Transient Response of 3-D Multi-Channel Nanowire MOSFETs Submitted to Heavy Ion Irradiation: a 3-D Simulation Study. IEEE Transactions on Nuclear Science, 2009, 56, 2042-2049.	2.0	15
70	Compact Modeling of Quasi-Ballistic Transport and Quantum Mechanical Confinement in Nanowire MOSFETs: Circuit Performances Analysis. , 2009, , .		5
71	Compact Modeling of Independent Double-Gate MOSFET: A Physical Approach. , 2009, , 27-54.		3
72	Modeling and Simulation of Single-Event Effects in Digital Devices and ICs. IEEE Transactions on Nuclear Science, 2008, 55, 1854-1878.	2.0	143

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73	Impact of Ballistic and Quasi-Ballistic Transport on Performances of Double-Gate MOSFET-Based Circuits. IEEE Transactions on Electron Devices, 2008, 55, 2443-2453.	3.0	27
74	Electron mean-free-path experimental extraction on ultra-thin and ultra-short strained and unstrained FDSOI n-MOSFETs. , 2008, , .		4
75	3-D simulation analysis of bipolar amplification in Planar Double-Gate and FinFET with independent gates. , 2008, , .		1
76	Altitude and underground real-time SER characterization of CMOS 65nm SRAM. , 2008, , .		2
77	Transient response of 3-D Multi-Channel nanowire MOSFETs submitted to heavy ion irradiation: A 3-D simulation study. , 2008, , .		1
78	A simple compact model to analyze the impact of ballistic and quasi-ballistic transport on ring oscillator performance. , 2008, , .		2
79	Real-time neutron and alpha soft-error rate testing of CMOS 130nm SRAM: Altitude versus underground measurements. , 2008, , .		14
80	Simulation Analysis of Quantum Confinement and Short-Channel Effects in Independent Double-Gate Metal-oxide-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2008, 47, 7013-7018.	1.5	14
81	Impact of Geometrical and Electrical Parameters on Speed Performance Characteristics in Ultimate Double-Gate Metal-oxide-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2008, 47, 3390-3395.	1.5	5
82	New Unified Analytical Model of Backscattering Coefficient From Low- to High-Field Conditions in Quasi-Ballistic Transport. IEEE Electron Device Letters, 2008, 29, 1392-1394.	3.9	11
83	A new unified compact model for quasi-ballistic transport: Application to the analysis of circuit performances of a Double-Gate architecture. , 2008, , .		3
84	Simulation of Electron Transport in Nanoscale Independent-Gate Double-Gate Devices Using a Full 2D Green's Function Approach. Journal of Computational and Theoretical Nanoscience, 2008, 5, 1120-1127.	0.4	30
85	Impact of high-permittivity dielectrics on speed performances and power consumption in double-gate-based CMOS circuits. Journal of Non-Crystalline Solids, 2007, 353, 639-644.	3.1	5
86	Altitude SEE Test European Platform (ASTEP) and First Results in CMOS 130 nm SRAM. IEEE Transactions on Nuclear Science, 2007, 54, 1002-1009.	2.0	30
87	3D Quantum Numerical Simulation of Single-Event Transients in Multiple-Gate Nanowire MOSFETs. IEEE Transactions on Nuclear Science, 2007, 54, 994-1001.	2.0	36
88	Will strain be useful for 10nm quasi-ballistic FDSOI devices? An experimental study. , 2007, , .		17
89	Compact modeling of symmetrical double-gate MOSFETs including carrier confinement and short-channel effects. Molecular Simulation, 2007, 33, 605-611.	2.0	5
90	Strained FDSOI CMOS technology scalability down to 2.5nm film thickness and 18nm gate length with a TiN/HfO <sub>2</sub> gate stack. , 2007, , .		27

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91	Experimental determination of the channel backscattering coefficient on 10 <sup>6</sup> –70nm-metal-gate Double-Gate transistors. Solid-State Electronics, 2007, 51, 537-542.	1.4	33
92	Analysis of 45-nm Multi-Gate Transistors Behavior Under Heavy Ion Irradiation by 3-D Device Simulation. IEEE Transactions on Nuclear Science, 2006, 53, 3265-3270.	2.0	17
93	Investigation of Quantum Effects in Ultra-Thin Body Single- and Double-Gate Devices Submitted to Heavy Ion Irradiation. IEEE Transactions on Nuclear Science, 2006, 53, 3363-3371.	2.0	34
94	Quantum Short-channel Compact Modelling of Drain-Current in Double-Gate MOSFET. Solid-State Electronics, 2006, 50, 680-686.	1.4	71
95	Influence of band structure on electron ballistic transport in silicon nanowire MOSFETs: An atomistic study. Solid-State Electronics, 2006, 50, 716-721.	1.4	96
96	Investigation of 30 nm Gate-All-Around MOSFET Sensitivity to Heavy Ions: A 3-D Simulation Study. IEEE Transactions on Nuclear Science, 2006, 53, 1950-1958.	2.0	21
97	Performance Degradation Induced by Fringing Field-Induced Barrier Lowering and Parasitic Charge in Double-Gate Metal-Oxide-Semiconductor Field-Effect Transistors with High- $\epsilon_r$ Dielectrics. Japanese Journal of Applied Physics, 2005, 44, 8362-8366.	1.5	7
98	Influence of Simulation Parameters on the Bipolar Amplification in Fully-Depleted SOI Technologies under Heavy-Ion Irradiations. European Conference on Radiation and Its Effects on Components and Systems, Proceedings of the, 2005, , .	0.0	1
99	An analytical subthreshold current model for ballistic quantum-wire double-gate MOS transistors. Molecular Simulation, 2005, 31, 179-183.	2.0	13
100	Simulation analysis of the bipolar amplification induced by heavy-ion irradiation in double-gate MOSFETs. IEEE Transactions on Nuclear Science, 2005, 52, 2137-2143.	2.0	21
101	Simulation analysis of the bipolar amplification in fully-depleted SOI technologies under heavy-ion irradiations. IEEE Transactions on Nuclear Science, 2005, 52, 1474-1479.	2.0	43
102	Compact model of the quantum short-channel threshold voltage in symmetric Double-Gate MOSFET. Molecular Simulation, 2005, 31, 831-837.	2.0	24
103	A simulation analysis of FIBL in decananometer Double-Gate MOSFETs with high- $\epsilon_r$ gate dielectrics. Journal of Non-Crystalline Solids, 2005, 351, 1897-1901.	3.1	17
104	Quantum short-channel compact model for the threshold voltage in double-gate MOSFETs with high-permittivity gate dielectrics. Journal of Non-Crystalline Solids, 2005, 351, 1911-1918.	3.1	37
105	Compact modeling of the threshold voltage in silicon nanowire MOSFET including 2D-quantum confinement effects. Molecular Simulation, 2005, 31, 839-843.	2.0	8
106	Electrical modeling and simulation of nanoscale MOS devices with a high-permittivity dielectric gate stack. Materials Research Society Symposia Proceedings, 2004, 811, 295.	0.1	0
107	Treatment of Point Defects in Nanowire MOSFETs Using the Nonequilibrium Green's Function Formalism. Journal of Computational Electronics, 2004, 3, 393-396.	2.5	7
108	Atomic-scale modeling of double-gate MOSFETs using a tight-binding Green's function formalism. Solid-State Electronics, 2004, 48, 567-574.	1.4	37

#	ARTICLE	IF	CITATIONS
109	Compact Modeling of Weak Inversion Generation Transients in SOI MOSFETs. Journal of the Electrochemical Society, 2004, 151, G396.	2.9	4
110	Two-dimensional modeling of quantum ballistic transport in ultimate double-gate SOI devices. Solid-State Electronics, 2003, 47, 1219-1225.	1.4	73
111	Modeling of quantum ballistic transport in double-gate devices with ultra-thin oxides. Journal of Non-Crystalline Solids, 2003, 322, 206-212.	3.1	1
112	Stretch-out of high-permittivity MOS capacitanceâ€“voltage curves resulting from a lateral non-uniform oxide charge distribution. Journal of Non-Crystalline Solids, 2003, 322, 219-224.	3.1	8
113	Tunneling Component of the Ballistic Current in Ultimate Double-Gate Devices. Electrochemical and Solid-State Letters, 2003, 6, G95.	2.2	1
114	Electrical characterization, modelling and simulation of MOS structures with high- k gate stacks. Series in Materials Science and Engineering, 2003, , .	0.1	0
115	Assessment of Anomalous Behavior in Hydrodynamic Simulation of CMOS Bulk and Partially Depleted SOI Devices. Journal of the Electrochemical Society, 2002, 149, G574.	2.9	4
116	Investigation of Nonstationary Transport and Quantum Effects in Realistic Deep Submicrometer Partially Depleted SOI Technology. Electrochemical and Solid-State Letters, 2002, 5, G29.	2.2	1
117	Modeling of drain current overshoot and recombination lifetime extraction in floating-body submicron SOI MOSFETs. IEEE Transactions on Electron Devices, 2002, 49, 1198-1205.	3.0	34
118	Impact of technological parameters on non-stationary transport in realistic 50 nm MOSFET technology. Solid-State Electronics, 2002, 46, 1045-1050.	1.4	6
119	DYNAMOS: a numerical MOSFET model including quantum-mechanical and near-interface trap transient effects. Solid-State Electronics, 2002, 46, 1051-1059.	1.4	5
120	Characterization of Silicon-on-Sapphire Material and Devices for Radio Frequency Applications. Journal of the Electrochemical Society, 2001, 148, G218.	2.9	2
121	A novel in-situ SOI characterization technique: the intrinsic point-probe MOSFET. IEEE Electron Device Letters, 2001, 22, 166-169.	3.9	17
122	A review of the pseudo-MOS transistor in SOI wafers: operation, parameter extraction, and applications. IEEE Transactions on Electron Devices, 2000, 47, 1018-1027.	3.0	185
123	Numerical simulation of the pseudo-MOSFET characterization technique. Solid-State Electronics, 1999, 43, 547-554.	1.4	13
124	Investigation of SOI MOSFETs with ultimate thickness. Microelectronic Engineering, 1999, 48, 339-342.	2.4	23
125	Model for the extraction of the recombination lifetime in partially depleted SOI MOSFETs. Microelectronic Engineering, 1999, 48, 355-358.	2.4	6
126	Circular Pseudo-Metal Oxide Semiconductor Field Effect Transistor in Silicon-on-Insulator Analytical Model, Simulation, and Measurements. Electrochemical and Solid-State Letters, 1999, 2, 242.	2.2	24



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127	Generation-recombination transient effects in partially depleted SOI transistors: systematic experiments and simulations. IEEE Transactions on Electron Devices, 1998, 45, 1678-1683.	3.0	66
128	Influence of Nitrogen or Argon Anneals on the Properties of Wafers and Devices Separated by Implantation of Oxygen. Journal of the Electrochemical Society, 1997, 144, 1468-1473.	2.9	4
129	Detailed characterization of Unibond material. Microelectronic Engineering, 1997, 36, 395-398.	2.4	14
130	Influence of Nitrogen or Argon Anneals on the Properties of Simox Wafers And Devices. Materials Research Society Symposia Proceedings, 1996, 446, 213.	0.1	0
131	A new lifetime characterization technique using drain current transients in SOI material. Solid-State Electronics, 1996, 39, 1753-1755.	1.4	15
132	Novel technique for carrier lifetime measurement by $\hat{f}^-$ -MOSFET transients. , 0, , .		0
133	3-D numerical simulation of the pseudo-MOS transistor. , 0, , .		0
134	The intrinsic pseudo-MOSFET technique. , 0, , .		0
135	Multiple transient effects in SOI transistors: Systematic measurements and simulation. , 0, , .		0
136	Non-stationary transport effects: impact on 0.1 $\hat{1}$ / <sub>4</sub> m PD SOI technology. , 0, , .		1
137	Atomic-scale modeling of source-to-drain tunneling in ultimate Schottky barrier double-gate MOSFETs. , 0, , .		9
138	Highly performant double gate MOSFET realized with SON process. , 0, , .		30
139	3D quantum modeling and simulation of multiple-gate nanowire MOSFETs. , 0, , .		29
140	Poly-gate replacement through contact hole (PRETCH): a new method for high-K/metal gate and multi-oxide implementation on chip. , 0, , .		7
141	Electrical characterization and modelling of high-performance SON DG MOSFETs. , 0, , .		7
142	Quantum short-channel compact modeling of drain-current in double-gate MOSFET. , 0, , .		10
143	Influence of band-structure on electron ballistic transport in silicon nanowire MOSFET's: an atomistic study. , 0, , .		14
144	Soft-Error Rate of Advanced SRAM Memories: Modeling and Monte Carlo Simulation. , 0, , .		17

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145	A 2-D/3-D Schrödinger-Poisson Drift-Diffusion Numerical Simulation of Radially-Symmetric Nanowire MOSFETs. , 0, , .		4
146	Investigation of Sensitivity to Heavy-Ion Irradiation of Junctionless Double-Gate MOSFETs by 3-D Numerical Simulation. , 0, , .		1
147	Charge Collection Physical Modeling for Soft Error Rate Computational Simulation in Digital Circuits. , 0, , .		4
148	Susceptibility of Group-IV and III-V Semiconductor-Based Electronics to Atmospheric Neutrons Explored by Geant4 Numerical Simulations. , 0, , .		5
149	Nanowires: Promising Candidates for Electrostatic Control in Future Nanoelectronic Devices. , 0, , .		4
150	Interactions between Terrestrial Cosmic-Ray Neutrons and III-V Compound Semiconductors. , 0, , .		2